

Technical documentation





SN74AXC2T45

SCES880C - AUGUST 2019 - REVISED JUNE 2021

SN74AXC2T45 2-Bit Translating Transceiver with Configurable Level-Shifting

1 Features

Texas

INSTRUMENTS

- Fully configurable dual-rail design allows each port to operate with a power supply range from 0.65 V to 3.6 V
- Operating temperature from -40°C to +125°C
- Glitch-free power supply sequencing
- Up to 380 Mbps support when translating from 1.8 V to 3.3 V
- V_{CC} isolation feature
 - If either V_{CC} input is below 100 mV, all I/Os outputs are disabled and become highimpedance
- Ioff supports partial-power-down mode operation
- Compatible with AVC family level shifters
- Latch-up performance exceeds 100 mA per JESD 78, Class II
- ESD protection exceeds JESD 22
 - 8000-V human-body model
 - 1000-V charged-device model

2 Applications

- Enterprise and communications
- Industrial
- Personal electronics
- Wireless infrastructure
- Building automation
- Point-of-sale

3 Description

The SN74AXC2T45 is a two-bit noninverting bus transceiver that uses two individually configurable power-supply rails. The device is operational with both V_{CCA} and V_{CCB} supplies as low as 0.65 V. The A port is designed to track V_{CCA} , which accepts any supply voltage from 0.65 V to 3.6 V. The B port is designed to track V_{CCB} , which also accepts any supply voltage from 0.65 V to 3.6 V. Additionally the SN74AXC2T45 is compatible with a single-supply system.

The SN74AXC2T45 device is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level of the direction-control input (DIR). The SN74AXC2T45 device is designed so the control pin (DIR) is referenced to V_{CCA} .

This device is fully specified for partial-power-down applications using the I_{off} current. The I_{off} protection circuitry ensures that no excessive current is drawn from or to an input, output, or combined I/O that is biased to a specific voltage while the device is powered down.

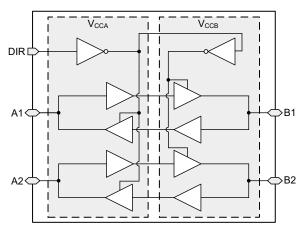
The V_{CC} isolation feature ensures that if either V_{CCA} or V_{CCB} is less than 100 mV, both I/O ports enter a high-impedance state by disabling their outputs.

Glitch-free power supply sequencing allows either supply rail to be powered on or off in any order while providing robust power sequencing performance.

Devic	Device information 4							
PART NUMBER	PACKAGE	BODY SIZE (NOM)						
SN74AXC2T45DCT	SM8 (8)	2.95 mm × 2.80 mm						
SN74AXC2T45DCU	VSSOP (8)	2.30 mm × 2.00 mm						
SN74AXC2T45DTM	X2SON (8)	1.35 mm × 0.80 mm						

Device Information⁽¹⁾

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Functional Block Diagram



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (January 2020) to Revision C (June 2021)	Page
 Updated the numbering format for tables, figures, and cross-references throughout the document Updated the <i>Enable Times</i> section	
Changes from Revision A (December 2019) to Revision B (January 2020)	Page
Added DCU and DCT packages to datasheet	1
Changes from Revision * (August 2019) to Revision A (December 2019)	Page

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•	Changed from	n Advance Informatior	n to Produc	ction Data		1



5 Pin Configuration and Functions

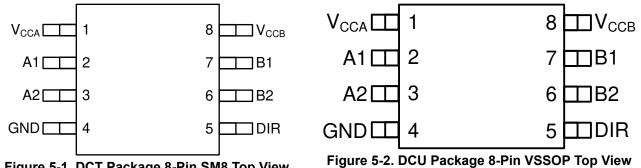


Figure 5-1. DCT Package 8-Pin SM8 Top View

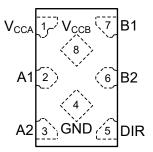


Figure 5-3. DTM Package 8-Pin X2SON Transpar	ent Top View
I Igure 5-5. DTM I ackage 5-1 III Azoon I Ianspar	

Table 5-1. Pin Functions

PIN	NO.	DESCRIPTION
NAME	DTM, DCU, DCT	DESCRIPTION
A1	2	Input/output A1. Referenced to V _{CCA} .
A2	3	Input/output A2. Referenced to V _{CCA} .
B1	7	Input/output B1. Referenced to V _{CCB} .
B2	6	Input/output B2. Referenced to V _{CCB} .
DIR	5	Direction-control in for both ports. Referenced to V _{CCA}
GND	4	Ground
V _{CCA}	1	A-port power supply voltage. 0.65 V \leq V _{CCA} \leq 3.6 V
V _{CCB}	8	B-port power supply voltage. 0.65 V \leq V _{CCB} \leq 3.6 V



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNITS
V_{CCA}	Supply voltage A		-0.5	4.2	V
V _{CCB}	Supply voltage B	-0.5	4.2	V	
		I/O Ports (A Port)	-0.5	4.2	
VI	Input Voltage ⁽²⁾	I/O Ports (B Port)	-0.5	4.2	v
		Control Inputs	-0.5	4.2	
Vo	Voltage applied to any output in the high-impedance or power-off state ⁽²⁾	A Port	-0.5	4.2	v
		B Port	-0.5	4.2	v
V	Voltage applied to any output in the high or low state ^{(2) (3)}	A Port	-0.5	V _{CCA} + 0.2 V _{CCB} + 0.2	v
Vo	Voltage applied to any output in the high of low state (-) (-)	B Port	-0.5	V _{CCB} + 0.2	
I _{IK}	Input clamp current	V _I < 0	-50		mA
I _{OK}	Output clamp current	V _O < 0	-50		mA
I _O	Continuous output current	l.	-50	50	mA
	Continuous current through V _{CC} or GND	-100	100	mA	
Tj	Junction Temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 4.2 V maximum if the output current rating is observed.

6.2 ESD Ratings

				VALUE	UNIT
			Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±8000	
ľ	V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC Specification JESD22-C101 ⁽²⁾	±1000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾ (2)

				MIN	MAX	UNIT	
V _{CCA}	Supply voltage A			0.65	3.6	V	
V _{CCB}	Supply voltage B			0.65	3.6	V	
			V _{CCI} = 0.65 V – 0.75 V	V _{CCI} × 0.70			
			V _{CCI} = 0.76 V – 1 V	V _{CCI} × 0.70			
		Data Inputs	V _{CCI} = 1.1 V – 1.95 V	V _{CCI} × 0.65			
			V _{CCI} = 2.3 V – 2.7 V	1.6			
V _{IL}			V _{CCI} = 3 V – 3.6 V	2			
	High-level input voltage		V _{CCA} = 0.65 V – 0.75 V	V _{CCA} × 0.70			
			V _{CCA} = 0.76 V – 1 V	V _{CCA} × 0.70			
		Control Input (DIR), Referenced to V _{CCA}	V _{CCA} = 1.1 V – 1.95 V	V _{CCA} × 0.65			
			V _{CCA} = 2.3 V – 2.7 V	1.6			
			V _{CCA} = 3 V – 3.6 V	2			
			V _{CCI} = 0.65 V – 0.75 V		V _{CCI} x 0.30		
		Data Inputs	V _{CCI} = 0.76 V – 1 V		V _{CCI} x 0.30		
			V _{CCI} = 1.1 V – 1.95 V		V _{CCI} x 0.35		
			V _{CCI} = 2.3 V – 2.7 V		0.7		
V	Low-level input voltage		V _{CCI} = 3 V – 3.6 V		0.8	V	
vIL	Low-level input voltage	-	V _{CCA} = 0.65 V – 0.75 V		$V_{CCA} \times 0.30$	v	
			V _{CCA} = 0.76 V – 1 V		$V_{CCA} \times 0.30$		
		Control Input (DIR), Referenced to V _{CCA}	V _{CCA} = 1.1 V – 1.95 V		V _{CCA} × 0.35		
			V _{CCA} = 2.3 V – 2.7 V		0.7		
			V _{CCA} = 3 V – 3.6 V		0.8		
VI	Input voltage			0	3.6	V	
V	Output voltage	Active State		0	V _{cco}	v	
۷O	Output voltage Tri-State			0	3.6	v	
Δt/Δv ⁽²⁾	Input transition rise and	fall time			10	ns/V	
$\Delta t / \Delta v^{(3)}$	Single channel input trar	nsition rise and fall time			100	ns/V	
T _A	Operating free-air tempe	rature		-40	125	°C	

(1)

 V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port. All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, (2) Implications of Slow or Floating CMOS Inputs, SCBA004.

Input transition rate of a single channel while the other channels are at a valid logic state and not switching. (3)

6.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	DCT (SM8)	DCU (VSSOP)	DTM (X2SON)	UNIT
R _{θJA}	Junction-to-ambient thermal resistance	223.5	242.9	225.9	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	120.7	96.2	131.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	138.0	153.3	141.3	°C/W
Y _{JT}	Junction-to-top characterization parameter	47.5	38.2	12.7	°C/W
Y _{JB}	Junction-to-board characterization parameter	136.7	152.5	140.9	°C/W

(1) For more information about thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

PARAMETER						Оре	erating free-ai	r tempera	ature (T _A)		
		TEST	CONDITIONS	V _{CCA}	V _{CCB}	-40°	C to 85°C	-40°	C to 125°C	;	
						MIN	TYP MAX	MIN	TYP I	MAX	
			I _{OH} = -100 μA	0.7 V – 3.6 V	0.7 V – 3.6 V	V _{CCO} -0.1		V _{CCO} -0.1			
			Ι _{ΟΗ} = -50 μΑ	0.65 V	0.65 V	0.55		0.55			
			I _{OH} = -200 μA	0.76 V	0.76 V	0.58		0.58			
	High-level		I _{OH} = -500 μA	0.85 V	0.85 V	0.65		0.65			
V _{он}	output voltage	$V_{I} = V_{IH}$	I _{OH} = -3 mA	1.1 V	1.1 V	0.85		0.85			V
			I _{OH} = -6 mA	1.4 V	1.4 V	1.05		1.05			
			I _{OH} = -8 mA	1.65 V	1.65 V	1.2		1.2			
			I _{OH} = -9 mA	2.3 V	2.3 V	1.75		1.75			
			I _{OH} = -12 mA	3 V	3 V	2.3		2.3			
			I _{OL} = 100 μA	0.7 V – 3.6 V	0.7 V – 3.6 V		0.1			0.1	
V _{OL}			I _{OL} = 50 μA	0.65 V	0.65 V		0.1			0.1	
			I _{OL} = 200 μA	0.76 V	0.76 V		0.18			0.18	
	Low-level output voltage		I _{OL} = 500 μA	0.85 V	0.85 V		0.2			0.2	V
		V _I = V _{IL}	I _{OL} = 3 mA	1.1 V	1.1 V		0.25			0.25	
			I _{OL} = 6 mA	1.4 V	1.4 V		0.35			0.35	
			I _{OL} = 8 mA	1.65 V	1.65 V		0.45			0.45	
			I _{OL} = 9 mA	2.3 V	2.3 V		0.55			0.55	
			I _{OL} = 12 mA	3 V	3 V		0.7			0.7	
		Control in V _{CCA} or (nput (DIR):V _I = GND	0.65 V – 3.6 V	0.65 V – 3.6 V	-0.5	0.5	-1		1	μA
I	current	Data Inp V _{CCI} or G	uts (Ax, Bx),V _I = GND	0.65 V – 3.6 V	0.65 V – 3.6 V	-4	4	-8		8	μA
	Partial power	A Port: V 3.6 V	$V_{\rm I}$ or $V_{\rm O}$ = 0 V –	0 V	0 V – 3.6 V	-4	4	-8		8	μA
off	down current	B Port: V 3.6 V	$V_{\rm I}$ or $V_{\rm O}$ = 0 V –	0 V – 3.6 V	0 V	-4	4	-8		8	μΑ
		V1 =		0.65 V – 3.6 V	0.65 V – 3.6 V		8			14	
CCA	V _{CCA} supply current	V _{CCI} or	I _O = 0	0 V	3.6 V	-2		-12			μA
	current	GND		3.6 V	0 V		4			8	
		V1 =		0.65 V – 3.6 V	0.65 V – 3.6 V		8			14	
ССВ	V _{CCB} supply current	V _{CCI} or	I _O = 0	0 V	3.6 V		4			8	μA
		GND		3.6 V	0 V	-2		-12			
сса + ссв	Combined supply current	V _I = V _{CCI} or GND	I _O = 0	0.65 V – 3.6 V	0.65 V – 3.6 V		16			23	μA
2 _i	Control Input (DIR) Capacitance	V _I = 3.3 V or GND		3.3 V	3.3 V		3.3		3.3		pF
C _{io}	Data I/O Capacitance	V _O = 1.6 -16 dBm	5 V DC +1 MHz sine wave	3.3 V	3.3 V		5.4		5.4		pF

(1) (2)

 V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port. All typical data is taken at 25°C.

(3)



6.6 Switching Characteristics, $V_{CCA} = 0.7 \pm 0.05 V$

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

										l	B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		^	В	-40°C to 85°C	0.5	170	0.5	115	0.5	84	0.5	50	0.5	50	0.5	56	0.5	71	0.5	106	
+	Propagation	A	D	-40°C to 125°C	0.5	170	0.5	115	0.5	84	0.5	50	0.5	50	0.5	56	0.5	71	0.5	106	ns
t _{pd}	delay	в	A	-40°C to 85°C	0.5	170	0.5	149	0.5	122	0.5	83	0.5	79	0.5	78	0.5	77	0.5	76	115
		В		-40°C to 125°C	0.5	170	0.5	149	0.5	122	0.5	83	0.5	79	0.5	78	0.5	77	0.5	76	
		DIR	A	-40°C to 85°C	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	
+	Disable time	DIR		-40°C to 125°C	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	0.5	140	ns
t _{dis}		DIR	в	-40°C to 85°C	0.5	143	0.5	105	0.5	84	0.5	41	0.5	39	0.5	42	0.5	56	0.5	107	115
		DIR		-40°C to 125°C	0.5	143	0.5	105	0.5	84	0.5	41	0.5	39	0.5	42	0.5	56	0.5	107	
		DIR	A	-40°C to 85°C	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	
+	Enable time	DIR		-40°C to 125°C	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	0.5	311	ne
t _{en}		DIR	В	-40°C to 85°C	0.5	306	0.5	247	0.5	216	0.5	186	0.5	182	0.5	183	0.5	194	0.5	228	ns
				-40°C to 125°C	0.5	306	0.5	247	0.5	216	0.5	186	0.5	182	0.5	183	0.5	194	0.5	228	

6.7 Switching Characteristics, V_{CCA} = 0.8 ± 0.04 V

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

											B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		A	в	-40°C to 85°C	0.5	150	0.5	94	0.5	63	0.5	33	0.5	28	0.5	27	0.5	28	0.5	34	
	Propagation		D	-40°C to 125°C	0.5	150	0.5	94	0.5	63	0.5	33	0.5	28	0.5	27	0.5	28	0.5	34	
t _{pd}	delay	в		-40°C to 85°C	0.5	115	0.5	94	0.5	76	0.5	50	0.5	41	0.5	40	0.5	38	0.5	38	ns
		B	A	-40°C to 125°C	0.5	115	0.5	94	0.5	76	0.5	50	0.5	41	0.5	40	0.5	38	0.5	38	
		DIR	A	-40°C to 85°C	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	
	Disable time		A	-40°C to 125°C	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	0.5	96	
t _{dis}		DIR	в	-40°C to 85°C	0.5	136	0.5	97	0.5	76	0.5	33	0.5	27	0.5	26	0.5	28	0.5	35	ns
			D	-40°C to 125°C	0.5	136	0.5	97	0.5	76	0.5	33	0.5	27	0.5	26	0.5	28	0.5	35	
		DIR	A	-40°C to 85°C	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	
t _{en}	Enable time		A	-40°C to 125°C	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	0.5	246	
^L en (1)		DIR	в	-40°C to 85°C	0.5	243	0.5	188	0.5	157	0.5	128	0.5	123	0.5	122	0.5	123	0.5	125	ns
				-40°C to 125°C	0.5	243	0.5	188	0.5	157	0.5	128	0.5	123	0.5	122	0.5	123	0.5	125	



6.8 Switching Characteristics, V_{CCA} = 0.9 \pm 0.045 V

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

											B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± (0.2 V	3.3 ± (0.3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		٨	в	-40°C to 85°C	0.5	122	0.5	76	0.5	51	0.5	23	0.5	18	0.5	16	0.5	15	0.5	17	
	Propagation	A	D	-40°C to 125°C	0.5	122	0.5	76	0.5	51	0.5	23	0.5	18	0.5	16	0.5	15	0.5	17	
t _{pd}	delay	в	A	-40°C to 85°C	0.5	84	0.5	63	0.5	51	0.5	39	0.5	28	0.5	24	0.5	21	0.5	21	ns
		В		-40°C to 125°C	0.5	84	0.5	63	0.5	51	0.5	39	0.5	28	0.5	24	0.5	21	0.5	21	
		DIR	A	-40°C to 85°C	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	
+	Disable time			-40°C to 125°C	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	0.5	74	nc
t _{dis}		DIR	в	-40°C to 85°C	0.5	133	0.5	94	0.5	73	0.5	30	0.5	23	0.5	22	0.5	20	0.5	22	ns
				-40°C to 125°C	0.5	133	0.5	94	0.5	73	0.5	31	0.5	24	0.5	22	0.5	20	0.5	23	
		DIR	A	-40°C to 85°C	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	
t _{en}	Enable time		A	-40°C to 125°C	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	0.5	211	
ι _{en} (1)		DIR	в	-40°C to 85°C	0.5	192	0.5	146	0.5	120	0.5	93	0.5	88	0.5	86	0.5	85	0.5	87	ns
				-40°C to 125°C	0.5	192	0.5	146	0.5	120	0.5	93	0.5	88	0.5	86	0.5	85	0.5	87	

6.9 Switching Characteristics, $V_{CCA} = 1.2 \pm 0.1 V$

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

										I	B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± ().1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		A	в	-40°C to 85°C	0.5	84	0.5	51	0.5	38	0.5	15	0.5	10	0.5	9	0.5	7	0.5	8	
+	Propagation			-40°C to 125°C	0.5	84	0.5	51	0.5	38	0.5	15	0.5	11	0.5	9	0.5	8	0.5	8	ns
τ _{pd}	delay	в	А	-40°C to 85°C	0.5	50	0.5	33	0.5	23	0.5	15	0.5	12	0.5	10	0.5	8	0.5	7	115
				-40°C to 125°C	0.5	50	0.5	33	0.5	23	0.5	15	0.5	12	0.5	10	0.5	8	0.5	7	
		DIR	A	-40°C to 85°C	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	
+	Disable time			-40°C to 125°C	0.5	27	0.5	27	0.5	27	0.5	27	0.5	27	0.5	27	0.5	27	0.5	27	ns
t _{dis}		DIR	в	-40°C to 85°C	0.5	129	0.5	90	0.5	70	0.5	27	0.5	20	0.5	18	0.5	15	0.5	15	115
				-40°C to 125°C	0.5	129	0.5	90	0.5	71	0.5	28	0.5	21	0.5	19	0.5	16	0.5	16	
		DIR	A	-40°C to 85°C	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	
t _{en}	Enable time			-40°C to 125°C	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	0.5	177	ns
(1)		DIR	В	-40°C to 85°C	0.5	105	0.5	71	0.5	59	0.5	40	0.5	36	0.5	35	0.5	33	0.5	34	115
				-40°C to 125°C	0.5	105	0.5	71	0.5	59	0.5	41	0.5	37	0.5	36	0.5	34	0.5	35	



6.10 Switching Characteristics, $V_{CCA} = 1.5 \pm 0.1 V$

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

											B-Port S	Supply	Voltage	(V _{ссв})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± ().1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		^	в	-40°C to 85°C	0.5	79	0.5	41	0.5	28	0.5	12	0.5	9	0.5	7	0.5	6	0.5	6	
+	Propagation	A	D	-40°C to 125°C	0.5	79	0.5	41	0.5	28	0.5	12	0.5	9	0.5	8	0.5	6	0.5	6	n 0
t _{pd}	delay	в	A	-40°C to 85°C	0.5	50	0.5	28	0.5	18	0.5	10	0.5	9	0.5	8	0.5	6	0.5	5	ns
		В		-40°C to 125°C	0.5	50	0.5	28	0.5	18	0.5	11	0.5	9	0.5	8	0.5	6	0.5	5	
		DIR	A	-40°C to 85°C	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	
+	Disable time		A	-40°C to 125°C	0.5	19	0.5	19	0.5	19	0.5	19	0.5	19	0.5	19	0.5	19	0.5	19	n 0
t _{dis}	Disable little	DIR	В	-40°C to 85°C	0.5	128	0.5	89	0.5	69	0.5	26	0.5	19	0.5	17	0.5	13	0.5	13	ns
			D	-40°C to 125°C	0.5	128	0.5	89	0.5	70	0.5	27	0.5	20	0.5	18	0.5	14	0.5	14	
		DIR	A	-40°C to 85°C	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	
t _{en}	Enable time		A	-40°C to 125°C	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	0.5	172	n 0
(1)		DIR	в	-40°C to 85°C	0.5	92	0.5	54	0.5	42	0.5	31	0.5	27	0.5	25	0.5	24	0.5	24	ns
			D	-40°C to 125°C	0.5	92	0.5	54	0.5	42	0.5	31	0.5	28	0.5	26	0.5	25	0.5	25	

6.11 Switching Characteristics, V_{CCA} = 1.8 ± 0.15 V

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

											B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		A	в	-40°C to 85°C	0.5	78	0.5	40	0.5	24	0.5	10	0.5	8	0.5	7	0.5	5	0.5	5	
	Propagation			-40°C to 125°C	0.5	78	0.5	40	0.5	24	0.5	10	0.5	8	0.5	7	0.5	6	0.5	5	na
t _{pd}	delay	в	^	-40°C to 85°C	0.5	56	0.5	27	0.5	16	0.5	9	0.5	7	0.5	7	0.5	5	0.5	4	ns
			A	-40°C to 125°C	0.5	56	0.5	27	0.5	16	0.5	9	0.5	8	0.5	7	0.5	5	0.5	5	
		DIR	A	-40°C to 85°C	0.5	16	0.5	16	0.5	16	0.5	16	0.5	16	0.5	16	0.5	16	0.5	16	
	Disable time			-40°C to 125°C	0.5	17	0.5	17	0.5	17	0.5	17	0.5	17	0.5	17	0.5	17	0.5	17	na
t _{dis}	Disable unie	DIR	в	-40°C to 85°C	0.5	127	0.5	88	0.5	69	0.5	25	0.5	18	0.5	16	0.5	12	0.5	12	ns
				-40°C to 125°C	0.5	127	0.5	88	0.5	70	0.5	26	0.5	19	0.5	17	0.5	13	0.5	13	
		DIR		-40°C to 85°C	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	
t _{en}	Enable time		A	-40°C to 125°C	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	0.5	171	na
(1)		DIR	в	-40°C to 85°C	0.5	89	0.5	50	0.5	36	0.5	26	0.5	23	0.5	22	0.5	21	0.5	20	ns
				-40°C to 125°C	0.5	89	0.5	50	0.5	36	0.5	27	0.5	24	0.5	23	0.5	22	0.5	21	



6.12 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2 V$

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

											B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		A	в	-40°C to 85°C	0.5	77	0.5	38	0.5	21	0.5	8	0.5	6	0.5	5	0.5	5	0.5	4	
+	Propagation		D	-40°C to 125°C	0.5	77	0.5	38	0.5	21	0.5	8	0.5	6	0.5	5	0.5	5	0.5	5	na
t _{pd}	delay	в	A	-40°C to 85°C	0.5	71	0.5	28	0.5	15	0.5	7	0.5	6	0.5	5	0.5	5	0.5	4	ns
		В		-40°C to 125°C	0.5	71	0.5	28	0.5	15	0.5	8	0.5	6	0.5	6	0.5	5	0.5	4	
		DIR	A	-40°C to 85°C	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	
+	Disable time		A	-40°C to 125°C	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	na
t _{dis}	Disable unie	DIR	в	-40°C to 85°C	0.5	127	0.5	88	0.5	68	0.5	25	0.5	18	0.5	15	0.5	12	0.5	11	ns
				-40°C to 125°C	0.5	127	0.5	88	0.5	69	0.5	26	0.5	19	0.5	16	0.5	12	0.5	12	
		DIR	A	-40°C to 85°C	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	
t _{en}	Enable time		A	-40°C to 125°C	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	0.5	182	na
ι _{en} (1)		DIR	в	-40°C to 85°C	0.5	84	0.5	46	0.5	29	0.5	18	0.5	17	0.5	16	0.5	15	0.5	15	ns
				-40°C to 125°C	0.5	84	0.5	46	0.5	29	0.5	19	0.5	18	0.5	17	0.5	16	0.5	16	

6.13 Switching Characteristics, V_{CCA} = 3.3 ± 0.3 V

See Figure 5 and Table 1 for test circuit and loading. See Figure 6, Figure 7, and Figure 8 for measurement waveforms.

											B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Condtions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		A	в	-40°C to 85°C	0.5	76	0.5	38	0.5	21	0.5	7	0.5	5	0.5	4	0.5	4	0.5	4	
	Propagation			-40°C to 125°C	0.5	76	0.5	38	0.5	21	0.5	7	0.5	5	0.5	5	0.5	4	0.5	4	ns
τ _{pd}	delay	в	А	-40°C to 85°C	0.5	105	0.5	34	0.5	17	0.5	8	0.5	6	0.5	5	0.5	4	0.5	4	115
				-40°C to 125°C	0.5	105	0.5	34	0.5	17	0.5	8	0.5	6	0.5	5	0.5	5	0.5	4	
		DIR	A	-40°C to 85°C	0.5	10	0.5	10	0.5	10	0.5	10	0.5	10	0.5	10	0.5	10	0.5	10	
t	Disable time			-40°C to 125°C	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	ns
t _{dis}		DIR	в	-40°C to 85°C	0.5	128	0.5	88	0.5	68	0.5	24	0.5	17	0.5	15	0.5	11	0.5	11	115
				-40°C to 125°C	0.5	128	0.5	88	0.5	69	0.5	26	0.5	19	0.5	16	0.5	12	0.5	11	
		DIR	A	-40°C to 85°C	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	
t _{en}	Enable time			-40°C to 125°C	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	0.5	218	n 0
(1)		DIR	в	-40°C to 85°C	0.5	83	0.5	45	0.5	28	0.5	17	0.5	15	0.5	14	0.5	14	0.5	14	ns
				-40°C to 125°C	0.5	83	0.5	45	0.5	28	0.5	18	0.5	16	0.5	15	0.5	15	0.5	15	

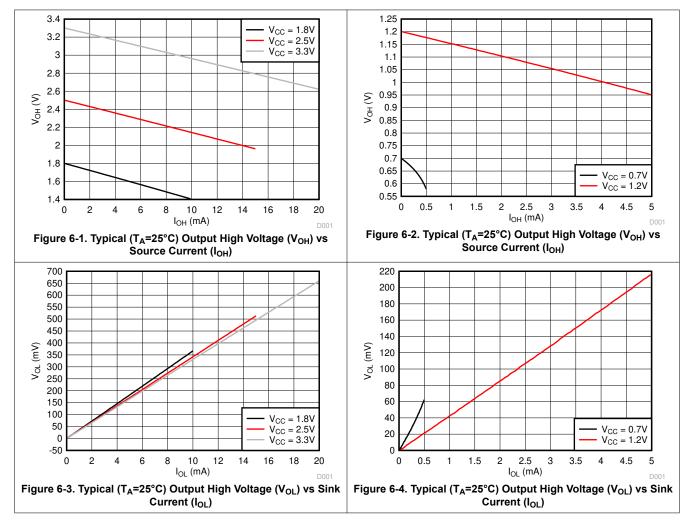


6.14 Operating Characteristics: T_A = 25°C

	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	MIN TYP	MAX	UNIT
			0.7 V	0.7 V	2.2		
			0.8 V	0.8 V	2.0		
			0.9 V	0.9 V	2.0		
	Power Dissipation Capacitance	CL = 0, RL = Open f = 1	1.2 V	1.2 V	2.0		
	per transceiver (A to B)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	2.0		pF
			1.8 V	1.8 V	2.1		
			2.5 V	2.5 V	2.5		
C			3.3 V	3.3 V	3.0		
C _{pdA}			0.7 V	0.7 V	10.6		
			0.8 V	0.8 V	10.7		
			0.9 V	0.9 V	10.6		
	Power Dissipation Capacitance	CL = 0, RL = Open f = 1	1.2 V	1.2 V	10.8		~ F
	per transceiver (B to A)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	11.1		pF
			1.8 V	1.8 V	12.2		
			2.5 V	2.5 V	15.9		
			3.3 V	3.3 V	19.6		
			0.7 V	0.7 V	10.6		
			0.8 V	0.8 V	10.7		
			0.9 V	0.9 V	10.6		
	Power Dissipation Capacitance	CL = 0, RL = Open f = 1	1.2 V	1.2 V	10.8		
	per transceiver (A to B)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	11.1		pF
			1.8 V	1.8 V	12.2		
			2.5 V	2.5 V	15.8		
			3.3 V	3.3 V	19.3		
C _{pdB}			0.7 V	0.7 V	2.2		
			0.8 V	0.8 V	2.0		
			0.9 V	0.9 V	2.0		
	Power Dissipation Capacitance	CL = 0, RL = Open f = 1	1.2 V	1.2 V	2.0		
	per transceiver (B to A)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	2.0		pF
			1.8 V	1.8 V	2.1		
			2.5 V	2.5 V	2.5		
			3.3 V	3.3 V	3.0		



6.15 Typical Characteristics



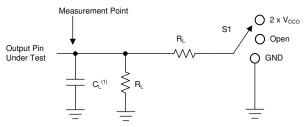


7 Parameter Measurement Information

7.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f = 1 MHz
- Z_O = 50 Ω
- dv/dt ≤ 1 ns/V

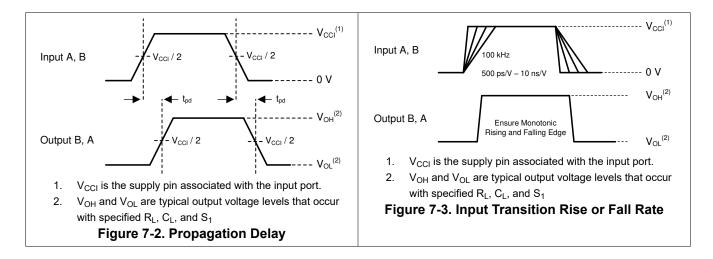


A. C_L includes probe and jig capacitance.

Figure 7-1. Load Circuit

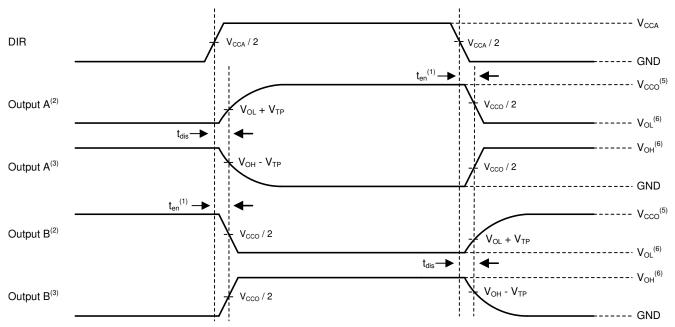
Table 7-1. Load Circuit Conditions

				Conditions		
	Parameter	V _{cco}	RL	CL	S ₁	V _{TP}
Δt/Δv	Input transition rise or fall rate	0.65 V – 3.6 V	1 MΩ	15 pF	Open	N/A
		1.1 V – 3.6 V	2 kΩ	15 pF	Open	N/A
t _{pd}	Propagation (delay) time	0.65 V – 0.95 V	20 kΩ	15 pF	Open	N/A
		3 V – 3.6 V	2 kΩ	15 pF	2 × V _{CCO}	0.3 V
	. Enable time, disable time	1.65 V – 2.7 V	2 kΩ	15 pF	2 × V _{CCO}	0.15 V
t _{en} , t _{dis}	dis Enable time, disable time	1.1 V – 1.6 V	2 kΩ	15 pF	$2 \times V_{CCO}$	0.1 V
		0.65 V – 0.95 V	20 kΩ	15 pF	2 × V _{CCO}	0.1 V
		3 V – 3.6 V	2 kΩ	15 pF	GND	0.3 V
		1.65 V – 2.7 V	2 kΩ	15 pF	GND	0.15 V
en, t _{dis}	Enable time, disable time	1.1 V – 1.6 V	2 kΩ	15 pF	GND	0.1 V
		0.65 V – 0.95 V	20 kΩ	15 pF	GND	0.1 V



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A. Illustrative purposes only. Enable Time is a calculation as described in the Application Information section.

B. Output waveform on the condition that input is driven to a valid Logic Low.

- C. Output waveform on the condition that input is driven to a valid Logic High.
- D. V_{CCI} is the supply pin associated with the input port.
- E. V_{CCO} is the supply pin associated with the output port.
- F. V_{OH} and V_{OL} are typical output voltage levels with specified R_L, C_L, and S₁.

Figure 7-4. Enable Time And Disable Time

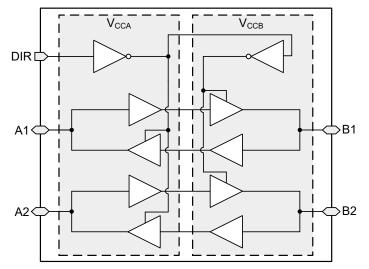


8 Detailed Description

8.1 Overview

The SN74AXC2T45 is a 2-bit, dual-supply non-inverting bidirectional voltage level translation device. Ax pins and the DIR pin are referenced to V_{CCA} logic levels, and Bx pins are referenced to V_{CCB} logic levels. The A port is able to accept I/O voltages ranging from 0.65 V to 3.6 V, while the B port can accept I/O voltages from 0.65 V to 3.6 V. A high on DIR enables data transmission from A to B and a low on DIR enables data transmission from B to A. See Device Functional Modes for a summary of the operation of the control logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in Section 6.5. The worst case resistance is calculated with the maximum input voltage, given in Section 6.1, and the maximum input leakage current, given in the Section 6.5, using Ohm's law ($R = V \div I$).

Signals applied to the inputs need to have fast edge rates, as defined by $\Delta t/\Delta v$ in Section 6.3 to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the standard CMOS input.

8.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in Section 6.1 must be followed at all times.

8.3.3 Partial Power Down (I_{off})

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in Section 6.5.

8.3.4 V_{CC} Isolation

The inputs and outputs for this device enter a high-impedance state when either supply is <100 mV.

8.3.5 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in Section 6.3.



8.3.6 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to V_{CC} when it should be held low). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral. For more information regarding the power up glitch performance of the AXC family of level translators, see the *Glitch Free Power Sequencing With AXC Level Translators* application report.

8.3.7 Negative Clamping Diodes

The inputs and outputs to this device have negative clamping diodes as depicted in Figure 8-1.

CAUTION

Voltages beyond the values specified in Section 6.1 table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

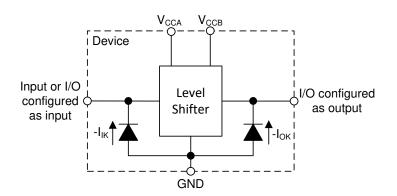


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.3.8 Fully Configurable Dual-Rail Design

Both the V_{CCA} and V_{CCB} pins can be supplied at any voltage from 0.65 V to 3.6 V, making the device suitable for translating between any of the voltage nodes (0.7 V, 0.8 V, 0.9 V, 1.2 V, 1.8 V, 2.5 V and 3.3 V).

8.3.9 Supports High-Speed Translation

The SN74AXC2T45 device can support high data-rate applications. The translated signal data rate can be up to 380 Mbps when the signal is translated from 1.8 V to 3.3 V.

8.4 Device Functional Modes

CONTROL INPUT	Port Status		OPERATION
DIR	A PORT	B PORT	OFERATION
L	Output (Enabled)	Input (Hi-Z)	B data to A bus
Н	Input (Hi-Z)	Output (Enabled)	A data to B bus

 Table 8-1. Function Table⁽¹⁾

(1) Input circuits of the data I/O's are always active.



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74AXC2T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The SN74AXC2T45 device is ideal for use in applications where a push-pull driver is connected to the data I/Os. The max data rate can be up to 380 Mbps when device translates a signal from 1.8 V to 3.3 V.

One example application is shown in Figure 9-1, where the SN74AXC2T45 device is used to translate low voltage error signals from a CPU to a higher voltage signal to properly drive the inputs of a system controller, thus alerting the system of any CPU errors such as overheating or other catastrophic processor errors.

9.1.1 Enable Times

Calculate the enable times for the SN74AXC2T45 using the following formulas:

$$t_{A_{en}} (DIR \text{ to } A) = t_{dis} (DIR \text{ to } B) + t_{pd} (B \text{ to } A)$$
(1)

$$t_{B_{en}} (DIR \text{ to } A) = t_{dis} (DIR \text{ to } A) + t_{pd} (A \text{ to } B)$$
(2)

In a bidirectional application, these enable times provide the maximum delay time from the time the DIR bit is switched until an output is expected. For example, if the SN74AXC2T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled (t_{dis}) before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay (t_{pd}) . To avoid bus contention care should be taken to not apply an input signal prior to the output port being disabled $(t_{dis} maximum)$.

9.2 Typical Application

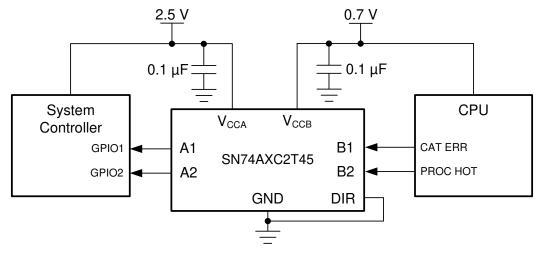


Figure 9-1. Processor Error Application



9.2.1 Design Requirements

For this design example, use the parameters listed in Table 9-1.

Table 9-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	0.65 V to 3.6 V
Output voltage range	0.65 V to 3.6 V

9.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- · Input voltage range
 - Use the supply voltage of the device that is driving the SN74AXC2T45 device to determine the input voltage range. For a valid logic-high, the value must exceed the high-level input voltage (V_{IH}) of the input port. For a valid logic low the value must be less than the low-level input voltage (V_{IL}) of the input port.
- Output voltage range
 - Use the supply voltage of the device that the SN74AXC2T45 device is driving to determine the output voltage range.

9.2.3 Application Curve

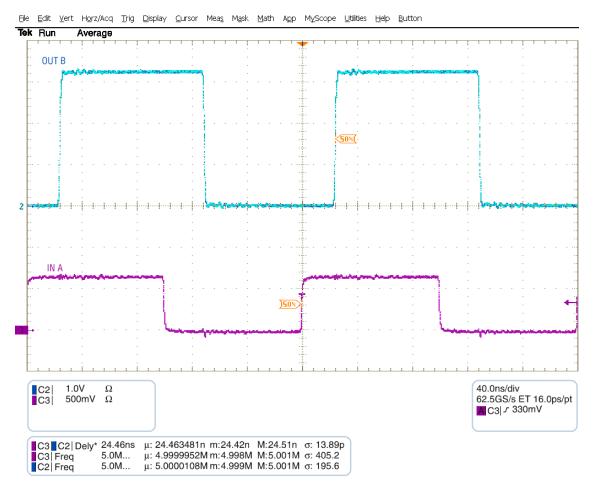


Figure 9-2. Up Translation at 2.5 MHz (0.7 V to 3.3 V)



10 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

This device is designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices. For more information regarding the power up glitch performance of the AXC family of level translators, see the *Glitch Free Power Sequencing With AXC Level Translators* application report

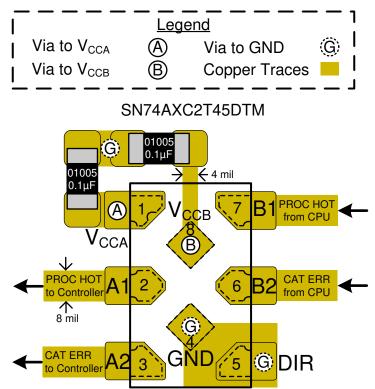
11 Layout

11.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines are recommended:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible. A 0.1 μF capacitor is recommended, but transient performance can be improved by having both 1 μF and 0.1 μF capacitors in parallel as bypass capacitors.
- Use short trace lengths to avoid excessive loading.

11.2 Layout Example





12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, Implications of Slow or Floating CMOS Inputs application report
- Texas Instruments, Power Sequencing for AXC Family of Devicesapplication report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material	(3)		(4/5)	
							(6)				
SN74AXC2T45DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(1H6, 2W7T) G	Samples
SN74AXC2T45DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	22HT	Samples
SN74AXC2T45DTMR	ACTIVE	X2SON	DTM	8	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1FP	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AXC2T45 :

Automotive : SN74AXC2T45-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

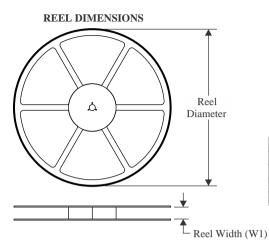


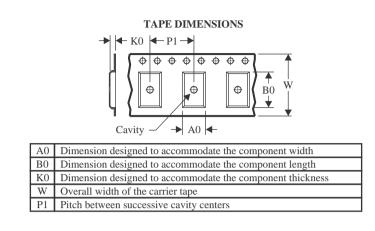
Texas

*All dimensions are nominal

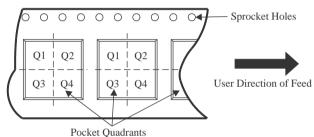
STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



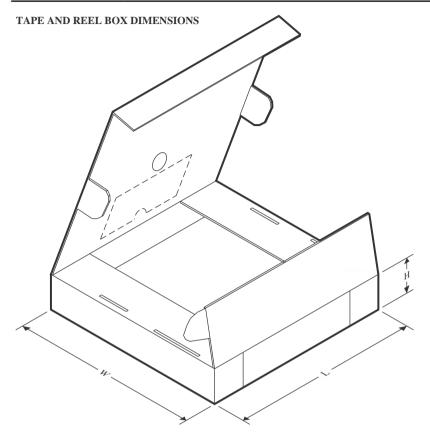
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AXC2T45DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
SN74AXC2T45DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74AXC2T45DTMR	X2SON	DTM	8	5000	178.0	8.4	0.93	1.49	0.43	2.0	8.0	Q1
SN74AXC2T45DTMR	X2SON	DTM	8	5000	180.0	9.5	0.93	1.49	0.43	2.0	8.0	Q1



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PACKAGE MATERIALS INFORMATION

16-Jun-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AXC2T45DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
SN74AXC2T45DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74AXC2T45DTMR	X2SON	DTM	8	5000	205.0	200.0	33.0
SN74AXC2T45DTMR	X2SON	DTM	8	5000	189.0	185.0	36.0

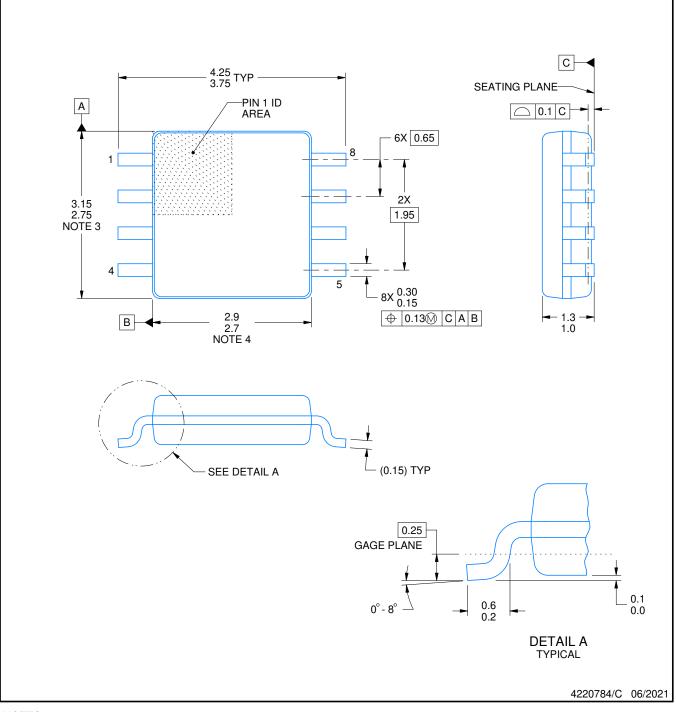
DCT0008A



PACKAGE OUTLINE

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.

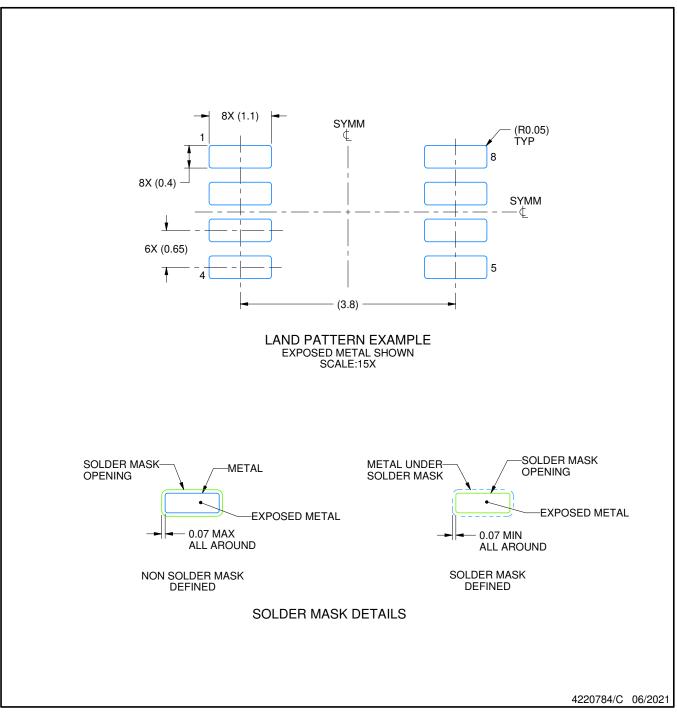


DCT0008A

EXAMPLE BOARD LAYOUT

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

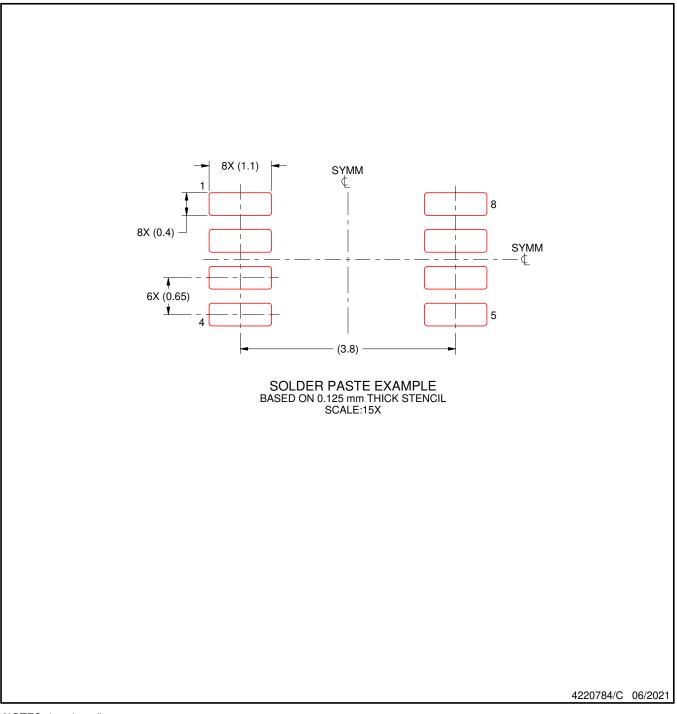


DCT0008A

EXAMPLE STENCIL DESIGN

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



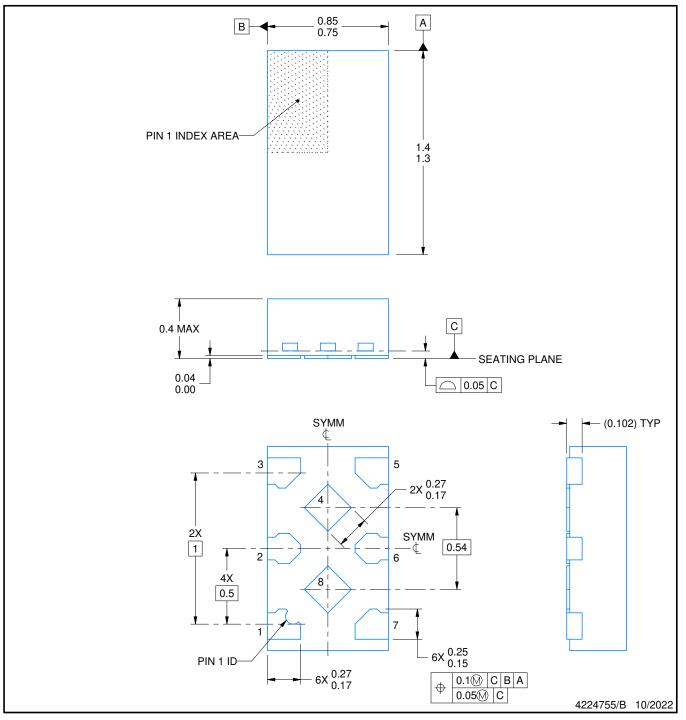
DTM0008A



PACKAGE OUTLINE

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.

3. The package thermal pad(s) must be soldered to the printed circuit board for thermal and mechanical performance.

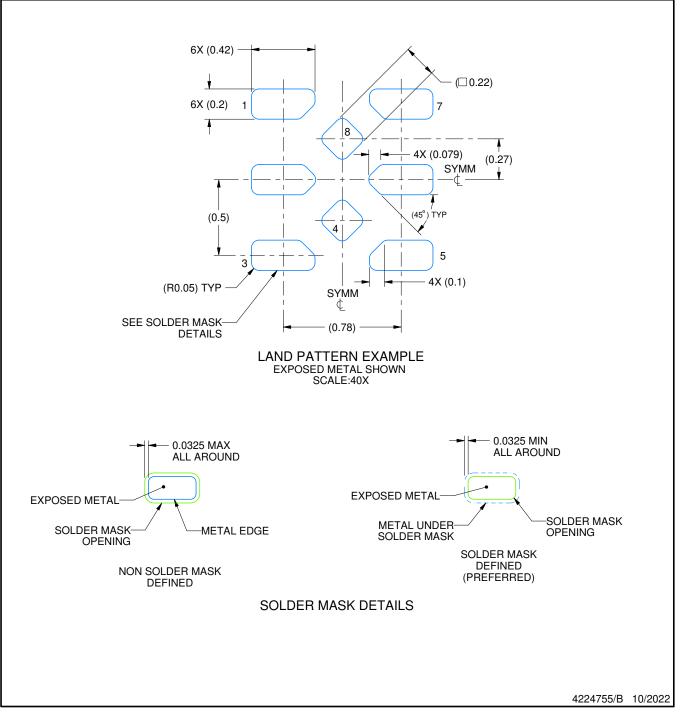


DTM0008A

EXAMPLE BOARD LAYOUT

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

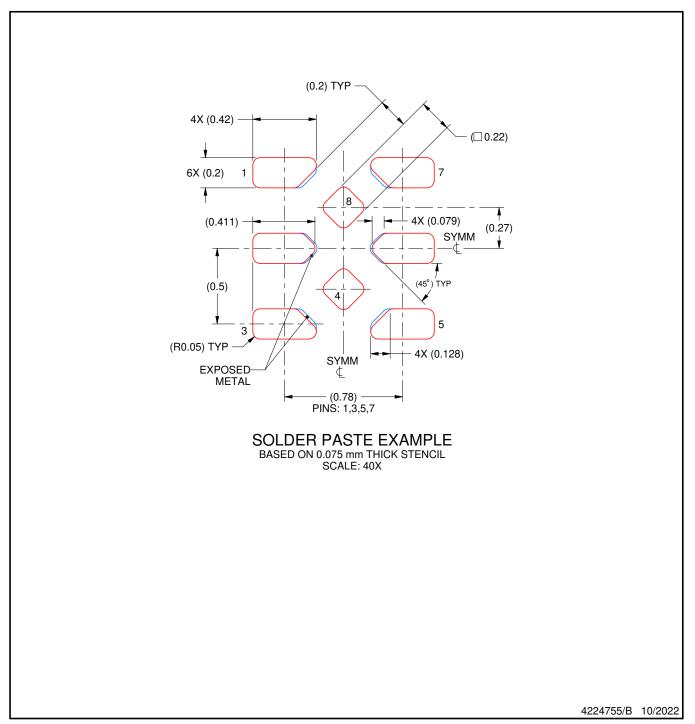


DTM0008A

EXAMPLE STENCIL DESIGN

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



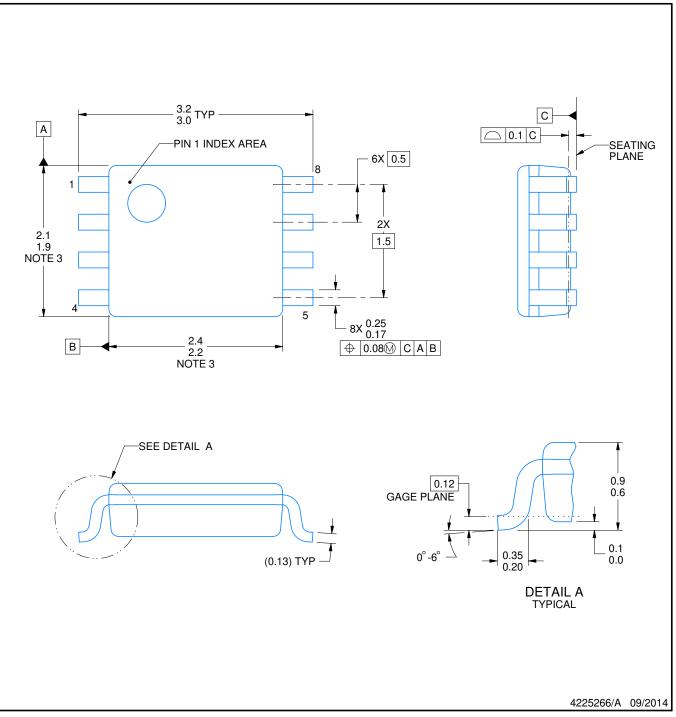
DCU0008A



PACKAGE OUTLINE

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side. 4. Reference JEDEC registration MO-187 variation CA.

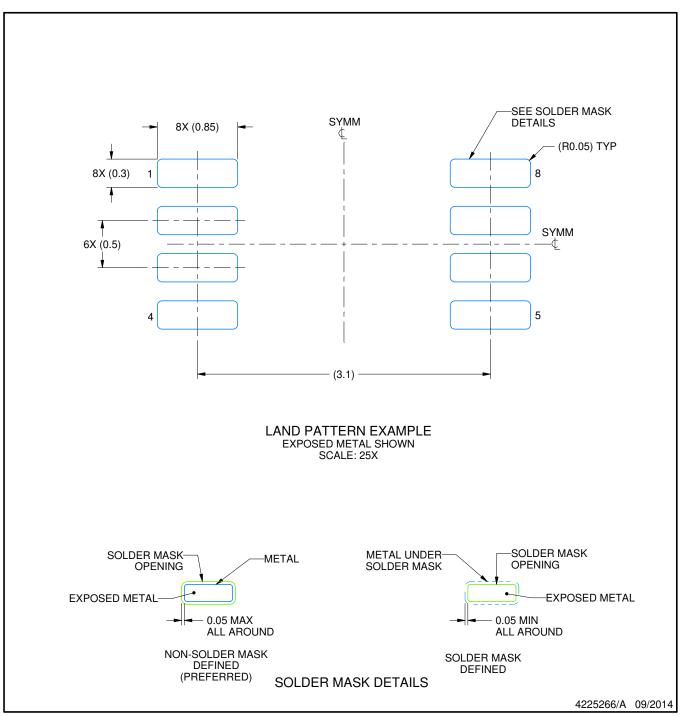


DCU0008A

EXAMPLE BOARD LAYOUT

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

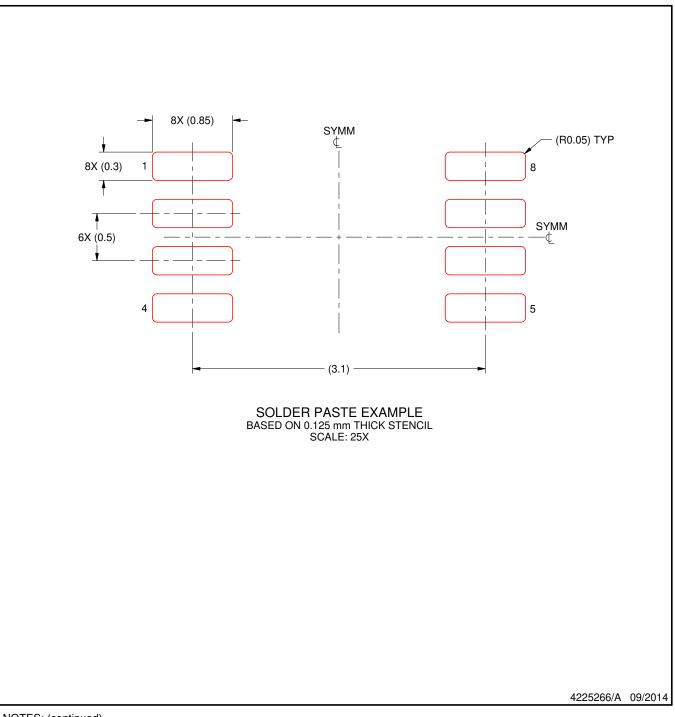


DCU0008A

EXAMPLE STENCIL DESIGN

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

8. Board assembly site may have different recommendations for stencil design.



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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